



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _A = +25°C
	155mΩ @ V _{GS} = -10V	-3.2A
-60V	240mΩ @ V _{GS} = -4.5V	-2.6A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

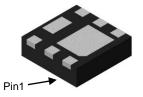
- Battery Management Application
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @
- Weight: 0.007 grams (Approximate)

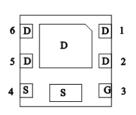
U-DFN2020-6 (Type F)



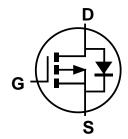


Bottom View

Top View



Pin Out Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP6250SFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel		
DMP6250SFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1:



5P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

zaio ccac rioj												
Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Site 2:



5P = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)
W = Week (ex: a = week 27; z represents week 52 and 53)
X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5		0	1	2	3	4	5	6	7	8	9
Week	Week 1-26					27-	-52		53			
Code		Α	λ-Z			a	-Z			7	Z	
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	٧	Х		Y		Z



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	lo	-3.2 -2.2	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	lo	-3.8 -2.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-12	Α
Continuous Source-Drain Diode Current (Note 6)	Is	-2	Α		
Avalanche Current (Note 7) L = 0.1mH	las	-12	A		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	D-	0.8	W
Total Fower Dissipation (Note 3)	$T_A = +70^{\circ}C$	PD	0.5	VV
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Rеja	156	°C/W
memial Resistance, Junction to Ambient (Note 3)	t<10s	Көја	121	C/VV
Total Bower Dissipation (Note 6)	$T_A = +25^{\circ}C$	D-	2.0	W
Total Power Dissipation (Note 6)	$T_A = +70^{\circ}C$	PD	1.3	VV
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Rеja	63	°C/W
mermal Resistance, Junction to Ambient (Note 6)	t<10s	Көја	43	C/VV
Thermal Resistance, Junction to Case	Steady State	Rejc	7.6	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

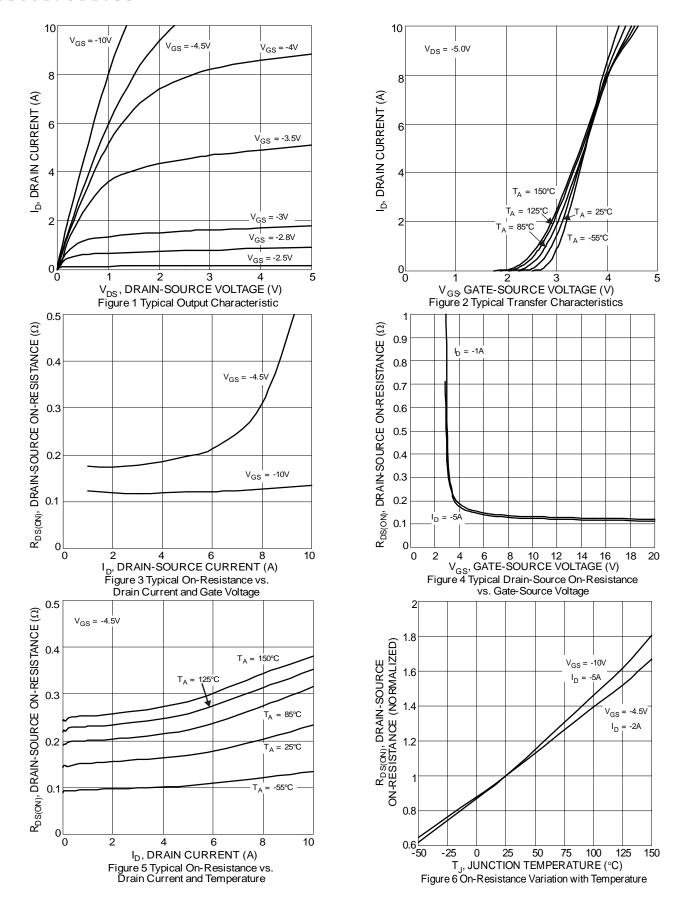
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BVDSS	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 16V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	Vgs(TH)	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	Dagger		_	155	mΩ	$V_{GS} = -10V, I_{D} = -2A$
Static Dialif-Source Off-Resistance	RDS(ON)		_	240	11122	$V_{GS} = -4.5V$, $I_{D} = -1A$
Diode Forward Voltage	VsD	l	-0.7	-1.2	V	$V_{GS} = 0V$, $I_{S} = -2A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss		612	_	pF	\/ 20\/ \/ 0\/
Output Capacitance	Coss		36	_	pF	$V_{DS} = -20V, V_{GS} = 0V,$ of = 1MHz
Reverse Transfer Capacitance	C _{rss}	l	26	l	pF	1 - 1101112
Gate Resistance	Rg	l	13	l	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -10V)	Q_{G}	_	8.9	_	nC	
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	l	4.3	-	nC	V _{DS} = -30V. I _D = -2A
Gate-Source Charge	Qgs		1.4	_	nC	VDS = -30V, ID = -2A
Gate-Drain Charge	Q_{GD}	_	1.7	_	nC	
Turn-On Delay Time	t _D (ON)	_	7.6	_	ns	
Turn-On Rise Time	t _R	_	11.6	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$
Turn-Off Delay Time	tD(OFF)	_	79.8	_	ns	$R_G = 50\Omega$, $I_D = -1A$
Turn-Off Fall Time	tF	_	37.8	_	ns	
Reverse Recovery Time	t _{RR}		10.8	_	ns	I _S = -1A, di/dt = 100A/μs
Reverse Recovery Charge	Qrr		3.8		nC	$I_S = -1A$, $di/dt = 100A/\mu s$

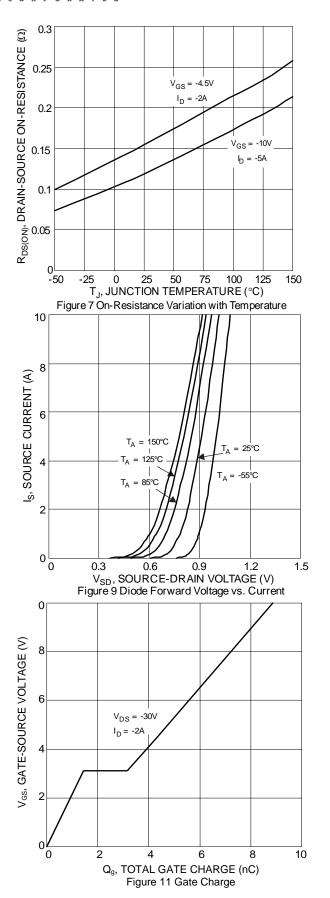
Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.









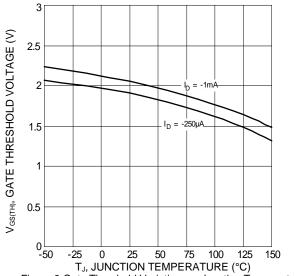
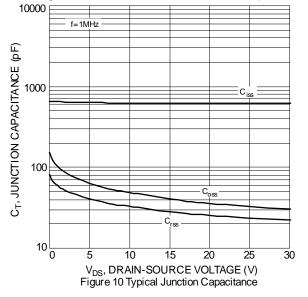


Figure 8 Gate Threshold Variation vs. Junction Temperature

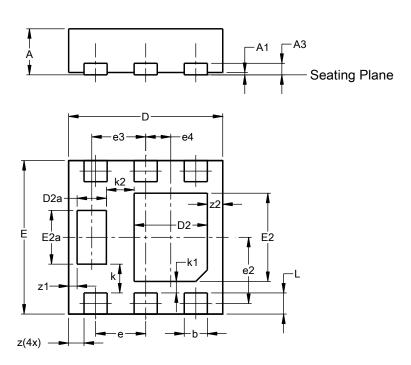




Package Outline Dimension

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

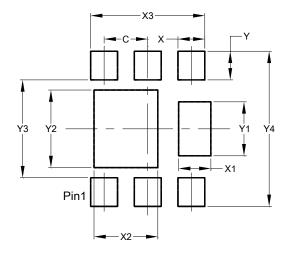


U-DFN2020-6										
	(Type F)									
Dim	Min	Max	Тур							
Α	0.57	0.63	0.60							
A1	0.00	0.05	0.03							
A3	-	-	0.15							
b	0.25	0.35	0.30							
D	1.95	2.05	2.00							
D2	0.85	1.05	0.95							
D2a	0.33	0.43	0.38							
Е	1.95	2.05	2.00							
E2	1.05	1.25	1.15							
E2a	0.65	0.75	0.70							
е	0.65 BSC									
e2	C).863 BS	SC							
e3		0.70 BS	С							
e4	C).325 BS	SC							
k		0.37 BS	С							
k1	0.15 BSC									
k2		0.36 BS	С							
L	0.225	0.325	0.275							
Z		0.20 BS								
z1	C).110 BS	SC							
z2		0.20 BS	С							
All D	imens	ions in	mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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